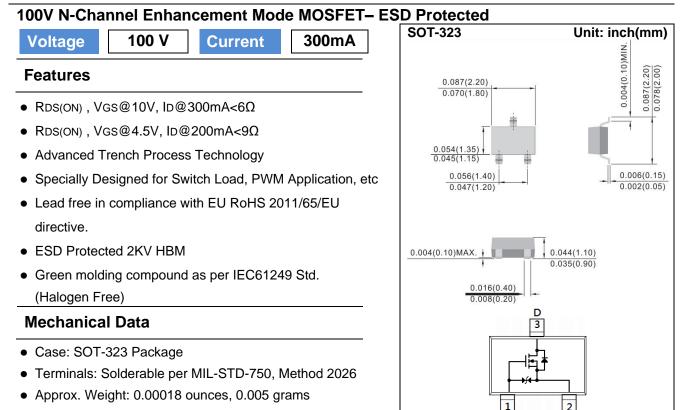
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Marking: C76

#### **Maximum Ratings and Thermal Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>GS</sub>	<u>+</u> 20	V	
Continuous Drain Current		I <sub>D</sub>	300	mA
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	800	mA
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	350	mW
	Derate above 25°C		2.8	mW/°C
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C
Typical Thermal resistance - Junction to Ambient <sup>(Note 3)</sup>		R <sub>θJA</sub>	357	°C/W



### **Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	1.5	1.77	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	V <sub>GS</sub> =10V, I <sub>D</sub> =300mA	-	4	6	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	-	4.2	9	Ω
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 10	uA
Dynamic (Note 5)						
Total Gate Charge	$Q_{g}$	$V_{DS}$ =30V, I <sub>D</sub> =200mA, $V_{GS}$ =10V <sup>(Note 1,2)</sup>	-	1.8	-	nC
Gate-Source Charge	$Q_gs$		-	0.4	-	
Gate-Drain Charge	$Q_gd$		-	0.3	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	45	-	pF
Output Capacitance	Coss		-	14	-	
Reverse Transfer Capacitance	Crss		-	7.8	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =30V, I <sub>D</sub> =200mA, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ <sup>(Note 1,2)</sup>	-	3.4	-	
Turn-On Rise Time	tr		-	19	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	8.2	-	ns
Turn-Off Fall Time	tf	K <sub>G</sub> =012	-	20	-	
Drain-Source Diode						•
Maximum Continuous Drain-Source					400	mA
Diode Forward Current	I <sub>S</sub>		-	-	400	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =400mA, V <sub>GS</sub> =0V	-	0.9	1.3	V

NOTES :

1. Pulse width300us, Duty cycle2%

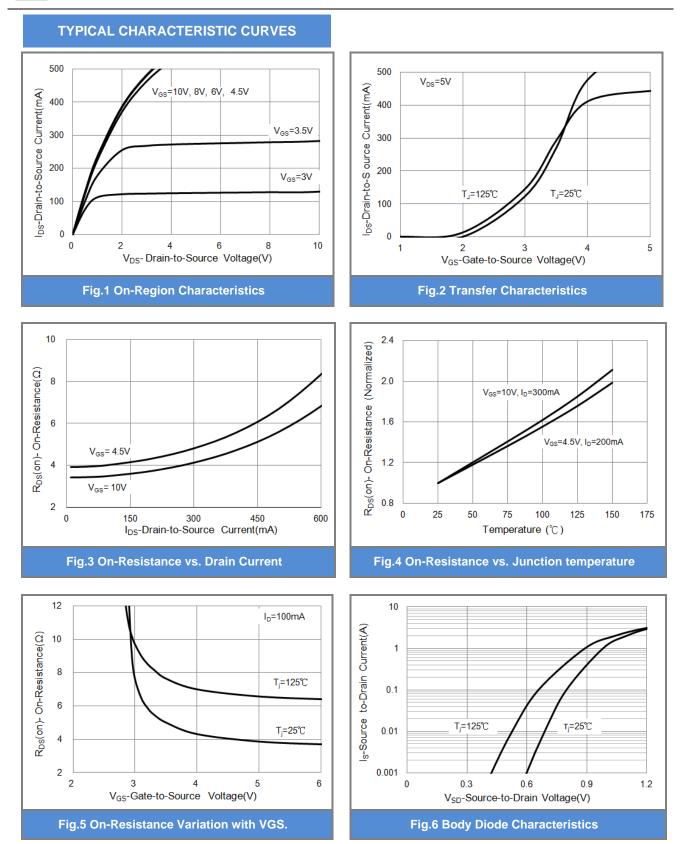
2. Essentially independent of operating temperature typical characteristics.

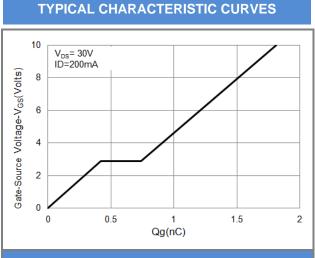
3. ReJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.

4. The maximum current rating is package limited.

5. Guaranteed by design, not subject to production testing.







#### Fig.7 Gate-Charge Characteristics

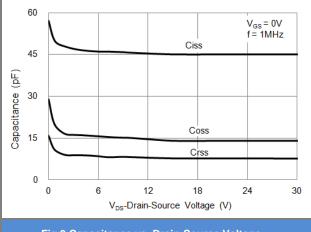
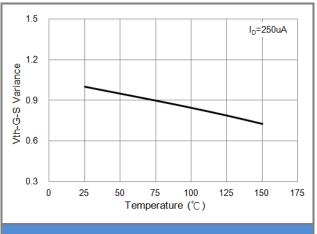


Fig.9 Capacitance vs. Drain-Source Voltage.





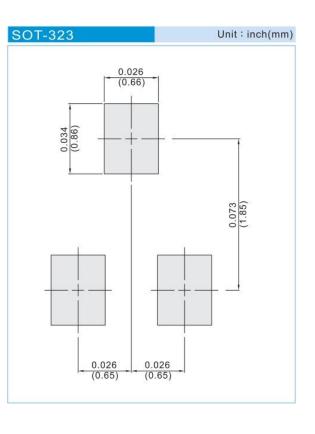




#### PART NO PACKING CODE VERSION

PART NO PACKING CODE	Package Type	Packing type	Marking	Version
PJC7476_R1_00001	SOT-323	3K pcs / 7" reel	C76	Halogen free
PJC7476_R2_00001	SOT-323	12K pcs / 7" reel	C76	Halogen free

#### MOUNTING PAD LAYOUT





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